NSN 5961-01-244-6748

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Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-244-6748 **Inclosure Material:** Metal **Overall Length:** 0.290 inches **Terminal Length:** 0.500 inches **Overall Diameter:** 0.230 inches **Internal Configuration:** Junction contact **Mounting Method: Terminal Terminal Circle Diameter:** 0.100 inches **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 50.0 collector to base voltage, dc and 30.0 collector to emitter voltage, dc and 7.0 emitter to base voltage, dc and 7.0 emitter to collector voltage, dc **Current Rating Per Characteristic:** 50.00 milliamperes collector current, dc **Power Rating Per Characteristic:** 250.0 milliwatts total power dissipation **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No